~~**What is claimed is:**~~

CLAIMS

1. A method for producing an electrical component, comprising:

~~providing a polyimide~~positioning an epoxy substrate;

coating at least one side of the ~~polyimide~~epoxy substrate with an adhesion layer comprising molybdenum, the adhesion layer comprising molybdenum being in direct contact with the epoxy substrate;

coating the adhesion layer with a copper seed layer, the copper seed layer being in direct contact with the adhesion layer comprising molybdenum;

covering at least a portion of the copper seed layer with a coating of photoresist;

removing a section of the coating of the photoresist to produce a surface feature;

performing a copper plating process wherein the surface feature is filled with copper;

removing the photoresist to produce a copper surface that comprises the at least a portion of the copper seed layer that was coated with the photoresist and the copper formed during the copper plating process;

~~performing a copper seed layer etching on the copper surface to produce copper etched surface; and~~

~~performing an adhesion layer etching on the copper etched surface.~~

after removing the photoresist, etching the copper surface to remove the at least a portion of the copper seed layer that was coated with the photoresist and leave at least a portion of the copper formed during the copper plating process; and

etching the adhesion layer exposed after etching the copper surface, wherein the adhesion layer is etched to have a width substantially equal to a width of the surface feature adjacent thereto.

2. The method according to claim 1, wherein etching the copper ~~etching is~~surface comprises a wet copper etching.

3. The method according to claim 1, wherein the removing of the section of the coating of the photoresist is performed through a photoresist developer.

4. The method according to claim 1, wherein the ~~polyimide~~epoxy substrate is ~~a polyimide~~an epoxy film~~, or wherein the molybdenum is molybdenum disulfide.~~.

5. The method according to claim 1, wherein the coating on the at least one side of the ~~polyimide~~epoxy substrate with an adhesion layer comprising molybdenum is performed by a sputtering process~~, and~~.

6. The method according to claim 5, wherein the sputtering process is produced by a magnetron.

~~6~~7. The method according to claim 1, wherein the molybdenum is molybdenum disulfide.

8. A method for producing an electrical component, comprising:

~~providing a polyimide~~positioning an epoxy substrate with an adhesion layer containing molybdenum disposed directly on the epoxy substrate and a copper seed layer disposed directly on the adhesion layer;

covering at least a portion of the copper seed layer with a coating of photoresist;

exposing the coating of photoresist, through a mask, to a radiation source;

removing a section of the coating of the photoresist to produce a surface feature transferred from the mask;

performing a copper plating process wherein the surface feature is filled with copper;

removing the photoresist to produce a copper surface~~;~~

~~performing~~ that comprises the at least a portion of the copper seed layer ~~etching on~~that was coated with the photoresist and the copper ~~surface to produce~~formed during the copper ~~etched surface; and~~plating process;

~~performing an adhesion layer etching on the copper etched surface.~~

~~7~~after removing the photoresist, etching the copper surface to remove the at least a portion of the copper seed layer that was coated with the photoresist and leave at least a portion of the copper formed during the copper plating process; and

etching the adhesion layer exposed after etching the copper surface, wherein the adhesion layer is etched to have a width substantially equal to a width of the surface feature adjacent thereto.

9. The method according to claim ~~6~~8, wherein etching the copper ~~etching is~~surface comprises a wet copper etching.

~~8~~10. The method according to claim ~~6~~8, wherein the removing of the section of the coating of the photoresist is performed through a photoresist developer.

~~9.~~

11. The method according to claim ~~6~~8, wherein the ~~polyimide~~epoxy substrate is ~~a polyimide~~an epoxy film~~, or wherein the molybdenum is molybdenum disulfide.~~.

~~10~~12. The method according to claim ~~6~~8, wherein the coating on at least one side of the ~~polyimide~~epoxy substrate with an adhesion layer comprising molybdenum is performed by a sputtering process~~, and wherein the sputtering process is produced by a magnetron~~.

13. The method according to claim 12, wherein the sputtering process is produced by a magnetron.

14. The method according to claim 8, wherein the molybdenum is molybdenum disulfide.

15. A method for producing an electrical component

~~11. An arrangement~~, comprising:

~~polyimide~~coating a first surface of an epoxy substrate with ~~a first surface;~~

~~a molybdenum~~an adhesion layer ~~connected to~~comprising molybdenum, the adhesion layer comprising molybdenum being in direct contact with the first surface of the epoxy substrate;

~~a seed layer connected to the molybdenum~~ coating the adhesion layer~~; and~~

~~with~~ a copper seed layer ~~connected to~~, the copper seed layer~~.~~

~~12. The arrangement according to claim 11~~, being in direct contact with the adhesion layer comprising molybdenum;

covering at least a portion of the copper seed layer with a coating of photoresist;

removing a section of the coating of the photoresist to produce a surface feature;

performing a copper plating process wherein the ~~seed layer~~ surface feature is ~~a~~ filled with copper;

removing the photoresist to produce a copper surface that comprises the at least a portion of the copper seed layer~~.~~ that was coated with the photoresist and the copper formed during the copper plating process;

after removing the photoresist, etching the copper surface to remove the at least a portion of the copper seed layer that was coated with the photoresist and leave at least a portion of the copper formed during the copper plating process; and

etching an exposed surface of the adhesion layer after etching the copper surface to expose the first surface of the epoxy substrate

~~13. The arrangement according to claim 11~~, wherein the ~~copper~~adhesion layer ~~has features that are at~~is etched to have a ~~line space packaging ratio~~width substantially equal to a width of ~~less than 10/10 μm~~the surface feature adjacent thereto.

~~14.~~

16. The ~~arrangement according to~~ method of claim ~~11~~15, wherein the ~~copper layer has features that are at a line space packaging ratio of less than 5/5 μm~~molybdenum is molybdenum disulfide.

~~15.~~

17. The ~~arrangement according to~~ method of claim ~~11~~15, wherein etching the copper surface comprises wet copper etching.

18. The method of claim 15, wherein the coating of the first surface of the epoxy substrate with an adhesion layer ~~has features that are at~~comprising molybdenum is performed by a ~~line space packaging ratio of less than 2/2 µm.~~sputtering process produced by a magnetron.